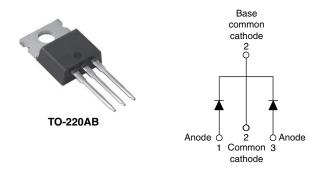


Vishay Semiconductors

Schottky Rectifier, 2 x 30 A



PRODUCT SUMMARY					
Package	TO-220AB				
I _{F(AV)}	2 x 30 A				
V _R	100 V				
V _F at I _F	0.69 V				
I _{RM} max.	20 mA at 125 °C				
T _J max.	175 °C				
Diode variation	Common cathode				
E _{AS}	11.25 mJ				

FEATURES

- 175 °C T_J operation
- Low forward voltage drop
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance



FREE

- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION

This center tap Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 175 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{F(AV)}	Rectangular waveform (per device)	60	А			
V _{RRM}		100	V			
I _{FRM}	T _C = 139 °C (per leg)	60	А			
I _{FSM}	t _p = 5 μs sine	1500	~			
V _F	30 A _{pk} , T _J = 125 °C	0.69	V			
TJ	Range	- 65 to 175	°C			

VOLTAGE RATINGS						
PARAMETER	SYMBOL	VS-63CTQ100PbF	VS-63CTQ100-N3	UNITS		
Maximum DC reverse voltage	V _R	100	100	V		
Maximum working peak reverse voltage	V _{RWM}	100	100	v		

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum averageper legforward currentper device			50 % duty avala at $T_{a} = 120$ %	rootangular wayoform	30		
		I _{F(AV)}	50 % duty cycle at T_C = 139 °C, rectangular waveform		60		
Peak repetitive forward current per leg		I _{FRM}	Rated V _R , square wave, 20 kHz, T _C = 140 °C		60	А	
Maximum peak one cycle non-repetitive surge current per leg		1	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated	1500		
		IFSM	10 ms sine or 6 ms rect. pulse	V _{RRM} applied	300		
Non-repetitive avalanche energy per leg		E _{AS}	T _J = 25 °C, I _{AS} = 0.75 A, L = 40 mH		11.25	mJ	
Repetitive avalanche current pe	er leg	I _{AR}	Current decaying linearly to zer Frequency limited by T_J maxim		0.75	А	

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ELECTRIC	CAL SPECIFI	CATIONS

PARAMETER	SYMBOL	TEST CONDITIONS			MAX.	UNITS
		30 A	T _{.1} = 25 °C	0.78	0.82	
Maximum forward voltage drop	V (1)	60 A	1j=25 C	0.94	1.0	V
	V _{FM} ⁽¹⁾	30 A	T _{.1} = 125 °C	0.64	0.69	
		60 A	1j = 125 C	0.78	0.83	
Maximum instantaneous reverse current	I _{RM}	T _J = 25 °C	Rated DC voltage	0.02	0.3	m 4
Maximum instantaneous reverse current		T _J = 125 °C	Rated DC voltage	11	20	mA
Maximum junction capacitance	CT	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		11	00	pF
Typical series inductance	Ls	Measured from top of terminal to mounting plane			.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R	10 000		V/µs	

Note

 $^{(1)}\,$ Pulse width < 300 $\mu s,\,duty\,cycle$ < 2 $\,\%$

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage	ge	T _J , T _{Stg}		- 65 to 175	°C	
Maximum thermal resistance junction to case per leg	,	R _{thJC}	R _{thJC} DC operation		°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	_{CS} Mounting surface, smooth and greased		0,11	
Approximate weight				2	g	
Approximate weight				0.07	oz.	
minimum			Non-lubricated threads	6 (5)	kgf ⋅ cm	
Mounting torque	maximum		Non-Iublicated threads		(lbf ⋅ in)	
Marking device			Case style TO-220AB	63CT	Q100	



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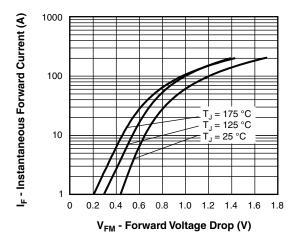


Fig. 1 - Maximum Forward Voltage Drop Characteristics

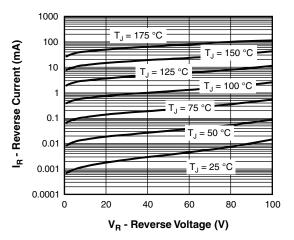


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

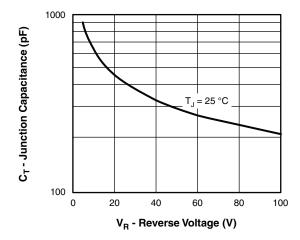
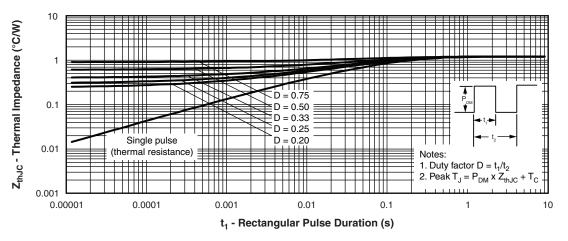


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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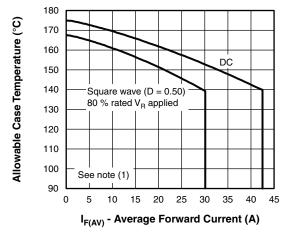
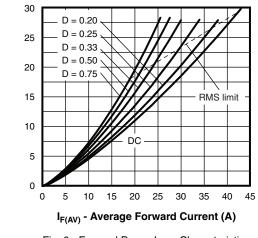
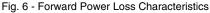
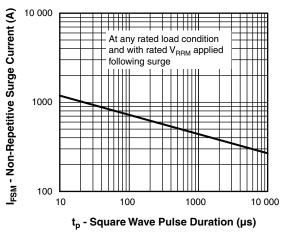


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current







Average Power Loss (W)

Fig. 7 - Maximum Non-Repetitive Surge Current (Per Leg)

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
 - $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see fig. 6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$



Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code	VS-	63	С	т	Q	100	PbF
I	1	2	3	4	5	6	7
1	-	Vishay	Semico	nductor	s produ	ct	
2	-	Curren	t rating	(60 A)			
3	-	Circuit	configui	ration			
		C = Common cathode					
4	-	Packag	je				
		T = TO	-220				
5	-	Schott	ky "Q" se	eries			
6	-	Voltage	e rating	(100 = 1	00 V)		
7	-	Enviro	nmental	digit			
		• PbF	= Lead	(Pb)-fre	e and R	oHS co	mpliant

• -N3 = Halogen-free, RoHS compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-63CTQ100PbF	50	1000	Antistatic plastic tube				
VS-63CTQ100-N3	50	1000	Antistatic plastic tube				

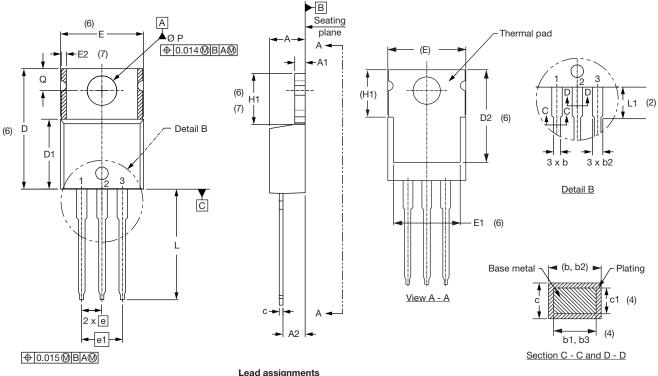
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -N3	www.vishay.com/doc?95028			

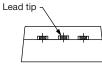


Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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